2nd TCT Workshop

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Jožef Stefan Institute

Book of Abstracts

Contents

TCT systems / 2

Advanced TCT systems

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TCT systems / 3

Two photon absorption Transient Current Technique System

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Practical issues(tips and tricks) / 4

Understanding pulse shapes at high fluences

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Practical issues(tips and tricks) / 5

TCT pulse anaysis and corrections

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New ways of using TCT / 6

Single event effect tests with focused light

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New ways of using TCT / 7

Laboratory results on LGADs (Timming)

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New ways of using TCT / 8

TCT in presence of continuos illumination - studies of bulk material

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Results from recent TCT measurements on different detector structures / 9

Edge TCT on AMS H35 HV-CMOS devices

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Results from recent TCT measurements on different detector structures / 10

TCT measurements on 3D detectors

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Results from recent TCT measurements on different detector structures / 11

Edge-TCT measurements

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Results from recent TCT measurements on different detector structures / 12

Mobility measurements

Practical issues(tips and tricks) / 13

Beam locator/Beam monitoring/Support PCBs

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Hands on experience / 14

Diode measurements and pulse analysis with TCT

1.) Analysis of the signal - reflection
2.) Mobility measurements

Hands on experience / 15

Scanning TCT - example of operation

1.) Beam condition monitoring at work (fibre split and in-beam version)
2.) Cabling issues and related problems
3.) Tunning the right signal
4.) Beam locator

Results from recent TCT measurements on different detector structures / 16

Edge-TCT measurements on different HVCMOS devices

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Results from recent TCT measurements on different detector structures / 17

Comparison of different simulations tools and update on KDet-Sim

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Results from recent TCT measurements on different detector structures / 18

TCAD simulations

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Results from recent TCT measurements on different detector structures / 19

Update on TRACS simulation

Simulations / 20

Comparison of different signal simulation tools

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Simulations / 21

TCAD simulations

Corresponding Author: marco.bomben@cern.ch

Simulations / 22

Update on TRACS

Corresponding Author: marcos.fernandez@cern.ch

Simulations / 23

Update on KDetSim

Corresponding Author: gregor.kramberger@ijs.si

Results from recent TCT measurements on different detector structures / 24

TCT measurements on diodes

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New ways of using TCT / 25

Resolving authentic time dependence of time-of-flight photocurrent in organic semiconductors

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Time-of-flight photoconductivity (TOF) is a powerful method, which is used to study conversion of photons to electrons and their transport through thin organic semiconductor layers. Compared to current-voltage characterization methods, TOF results are unaffected by the spurious effects at the semiconductor/metal interfaces. Precise knowledge of photocurrent time-dependence is of crucial importance for the determination of charge transport parameters such as mobility and the width of charge transporting states. Our TOF measurements of single-crystals of dioctyl-benzothieno-benzothiophene (C8-BTBT) show that transport of photexcited carriers and the corresponding photocurrent across two coplanar metal contacts separated by 120 μm, occurs in a fraction of a microsecond. However, measured time-dependent photocurrent (I(t)), compared to theoretical predictions, showed additional peaks and significant broadening of the I(t) lineshape. We found that additional peaks correspond to signal reflections from the waveguide terminations. And peaks broadening occurs due to 3-ns duration of the photoexcitation laser. Direct deconvolution of the measured signal was not possible due to signal reflections and relatively high noise-to-signal ratio. Therefore we estimated a time dependence of the photocurrent, which reproduced the measured signal transient. Estimated I(t) was considered as an authentic TOF response of the material under investigation.

Results from recent TCT measurements on different detector structures / 26

Temperature dependance of LGAD response

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27

Welcome